

# Phase Control Thyristor

## Types N0180SH120 to N0180SH160

### Absolute Maximum Ratings

	<b>VOLTAGE RATINGS</b>	<b>MAXIMUM LIMITS</b>	<b>UNITS</b>
$V_{DRM}$	Repetitive peak off-state voltage, (note 1)	1200-1600	V
$V_{DSM}$	Non-repetitive peak off-state voltage, (note 1)	1200-1600	V
$V_{RRM}$	Repetitive peak reverse voltage, (note 1)	1200-1600	V
$V_{RSM}$	Non-repetitive peak reverse voltage, (note 1)	1300-1700	V

	<b>OTHER RATINGS</b>	<b>MAXIMUM LIMITS</b>	<b>UNITS</b>
$I_{T(AV)}$	Mean on-state current, $T_{sink}=55^{\circ}C$ , (note 2)	180	A
$I_{T(AV)}$	Mean on-state current, $T_{sink}=85^{\circ}C$ , (note 2)	110	A
$I_{T(RMS)}$	Nominal RMS on-state current, $T_{sink}=25^{\circ}C$ , (note 2)	175	A
$I_{T(D.C.)}$	D.C. on-state current, $T_{sink}=25^{\circ}C$ , (note 4)	175	A
$I_{TSM}$	Peak non-repetitive surge $t_p=10ms$ , $V_{RM}=0.6V_{RRM}$ , (note 5)	2450	A
$I_{TSM2}$	Peak non-repetitive surge $t_p=10ms$ , $V_{RM}\leq 10V$ , (note 5)	2695	A
$I^2t$	$I^2t$ capacity for fusing $t_p=10ms$ , $V_{RM}=0.6V_{RRM}$ , (note 5)	$30\times 10^3$	$A^2s$
$I^2t$	$I^2t$ capacity for fusing $t_p=10ms$ , $V_{RM}\leq 10V$ , (note 5)	$36.3\times 10^3$	$A^2s$
$(di/dt)_{cr}$	Maximum rate of rise of on-state current (repetitive), (Note 6)	500	$A/\mu s$
	Maximum rate of rise of on-state current (non-repetitive), (Note 6)	1000	$A/\mu s$
$V_{FGM}$	Peak forward gate voltage	12	V
$I_{FGM}$	Peak forward gate current	19	A
$V_{RGM}$	Peak reverse gate voltage	5	V
$P_{G(AV)}$	Mean forward gate power	2	W
$P_{GM}$	Peak forward gate power (100 $\mu s$ pulse width)	100	W
$V_{GD}$	Non-trigger gate voltage, (Note 7)	0.25	V
$T_{HS}$	Operating temperature range	-40 to +125	$^{\circ}C$
$T_{stg}$	Storage temperature range	-40 to +150	$^{\circ}C$

**Notes:-**

- 1) De-rating factor of 0.13% per  $^{\circ}C$  is applicable for  $T_j$  below  $25^{\circ}C$ .
- 2) Double side cooled, single phase; 50Hz,  $180^{\circ}$  half-sinewave.
- 3) Single side cooled, single phase; 50Hz,  $180^{\circ}$  half-sinewave.
- 4) Double side cooled.
- 5) Half-sinewave,  $125^{\circ}C$   $T_j$  initial.
- 6)  $V_D=80\% V_{DRM}$ ,  $I_{FG}=1A$ ,  $t_r\leq 1\mu s$ ,  $T_{case}=125^{\circ}C$ .
- 7) Rated  $V_{DRM}$ .

### Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
$V_{TM}$	Maximum peak on-state voltage	-	-	1.57	$I_{TM}=715A$	V
$V_{T0}$	Threshold voltage	-	-	0.9		V
$r_T$	Slope resistance	-	-	1.79		mΩ
$(dv/dt)_{cr}$	Critical rate of rise of off-state voltage	1000	-	-	$V_D=80\% V_{DRM}$	V/μs
$I_{DRM}$	Peak off-state current	-	-	20	Rated $V_{DRM}$	mA
$I_{RRM}$	Peak reverse current	-	-	20	Rated $V_{RRM}$	mA
$V_{GT}$	Gate trigger voltage	-	-	3.0	$T_j=25^\circ C$	V
$I_{GT}$	Gate trigger current	-	-	150	$T_j=25^\circ C$ $V_D=6V, I_T=1A$	mA
$I_H$	Holding current	-	-	600	$T_j=25^\circ C$	mA
$R_{thJC}$	Thermal resistance, junction to case	-	-	0.23	Double side cooled	K/W
F	Mounting torque	-	-	14		Nm
$W_t$	Weight	-	130	-		g

Notes:-

- 1) Unless otherwise indicated  $T_j=125^\circ C$ .

**Notes on Ratings and Characteristics**

1.0 Voltage Grade Table

Voltage Grade	$V_{DRM}$ $V_{DSM}$ $V_{RRM}$ V	$V_{RSM}$ V	$V_D$ $V_R$ DC V
12	1200	1300	810
14	1400	1500	930
16	1600	1700	1040

2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for  $T_j$  below 25°C.

4.0 Repetitive dv/dt

Standard dv/dt is 1000V/μs.

5.0 Snubber Components

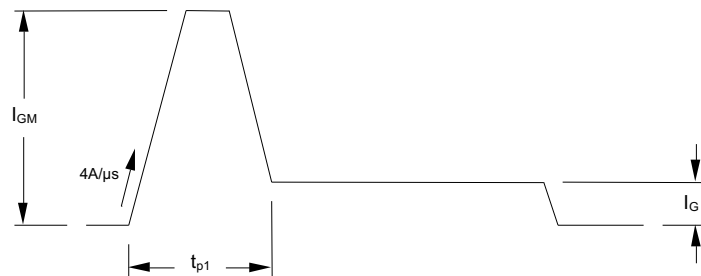
When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

6.0 Rate of rise of on-state current

The maximum un-primed rate of rise of on-state current must not exceed 1000A/μs at any time during turn-on on a non-repetitive basis. For repetitive performance, the on-state rate of rise of current must not exceed 500A/μs at any time during turn-on. Note that these values of rate of rise of current apply to the total device current including that from any local snubber network.

7.0 Gate Drive

The nominal requirement for a typical gate drive is illustrated below. An open circuit voltage of at least 30V is assumed. This gate drive must be applied when using the full di/dt capability of the device.



The magnitude of  $I_{GM}$  should be between five and ten times  $I_{GT}$ , which is shown on page 2. Its duration ( $t_{p1}$ ) should be 20μs or sufficient to allow the anode current to reach ten times  $I_L$ , whichever is greater. Otherwise, an increase in pulse current could be needed to supply the necessary charge to trigger. The 'back-porch' current  $I_G$  should remain flowing for the same duration as the anode current and have a magnitude in the order of 1.5 times  $I_{GT}$ .

**Curves**

Figure 1 - On-state characteristics of Limit device

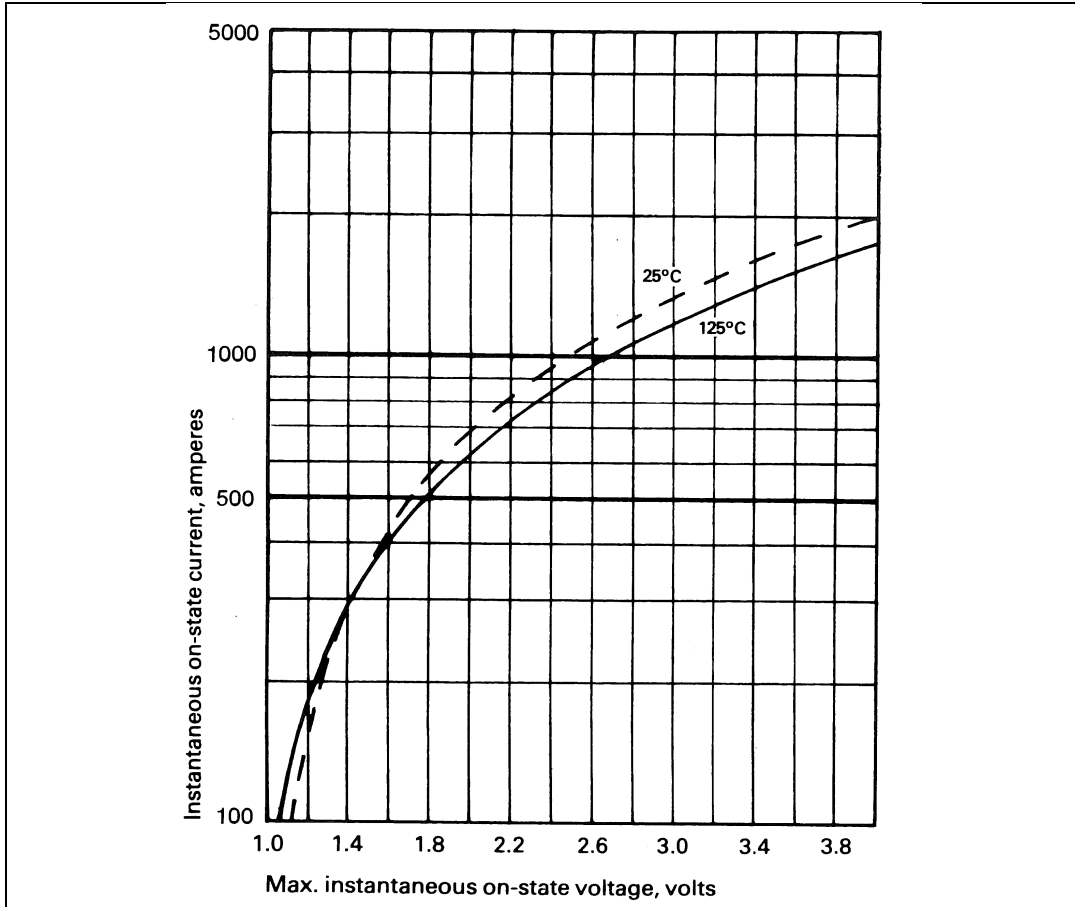


Figure 2 - Transient thermal impedance

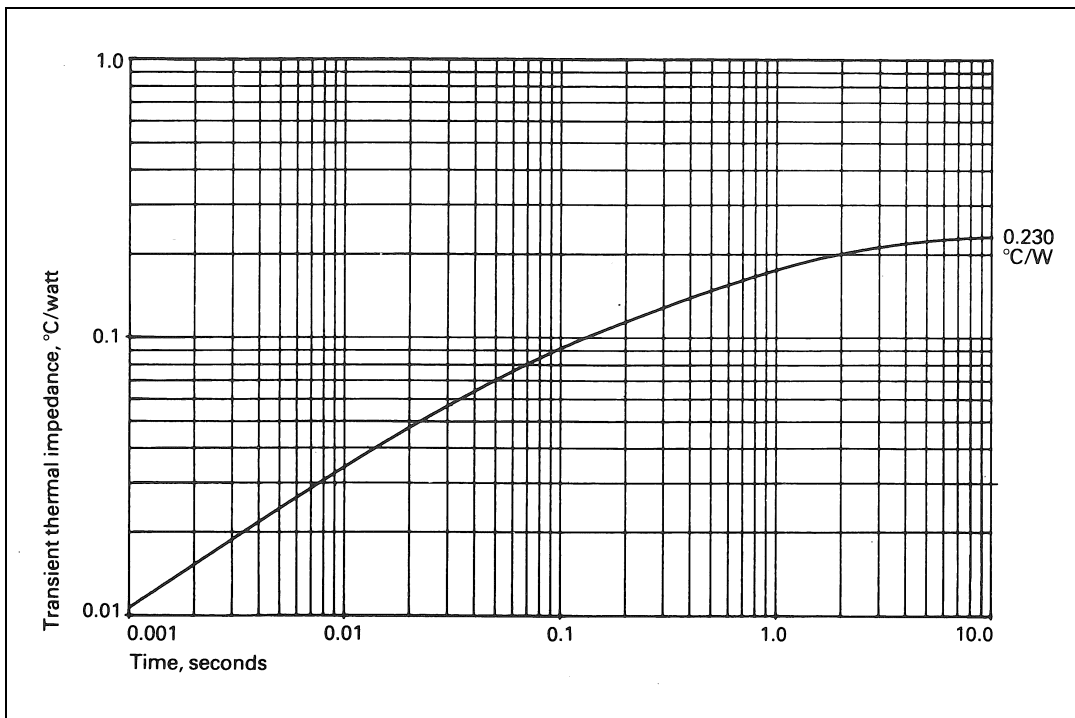


Figure 3 - Gate characteristics at 25°C junction temperature

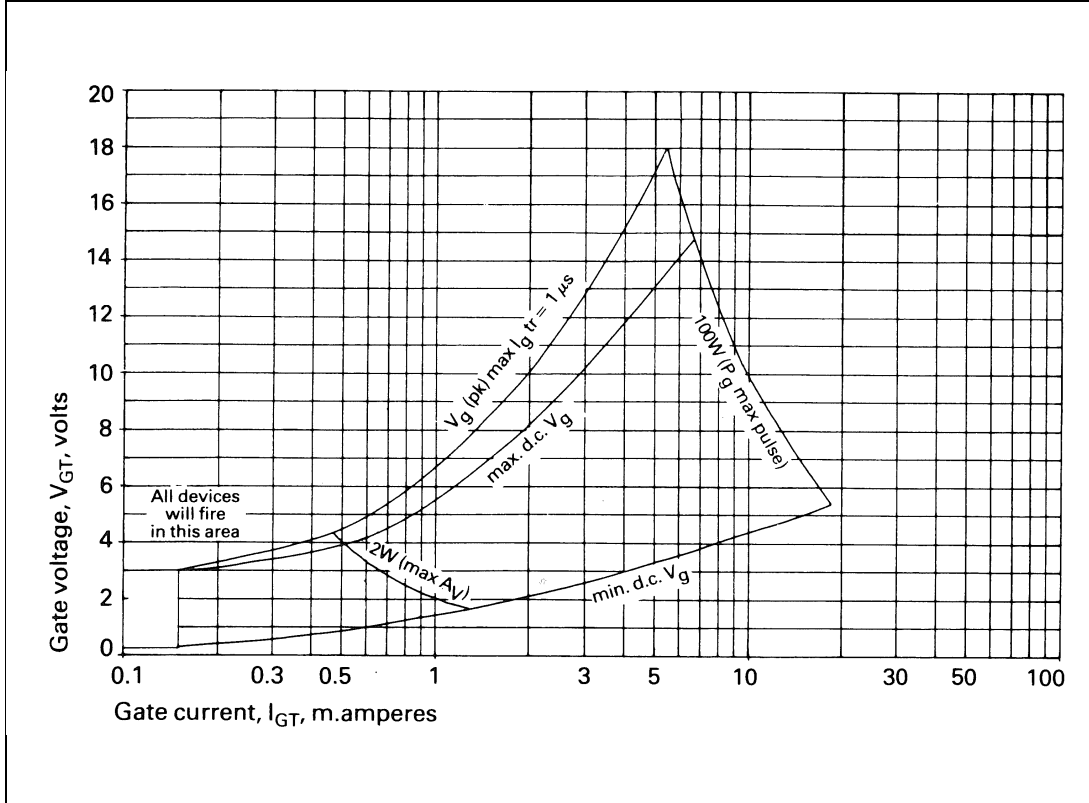


Figure 4 - Gate trigger characteristic

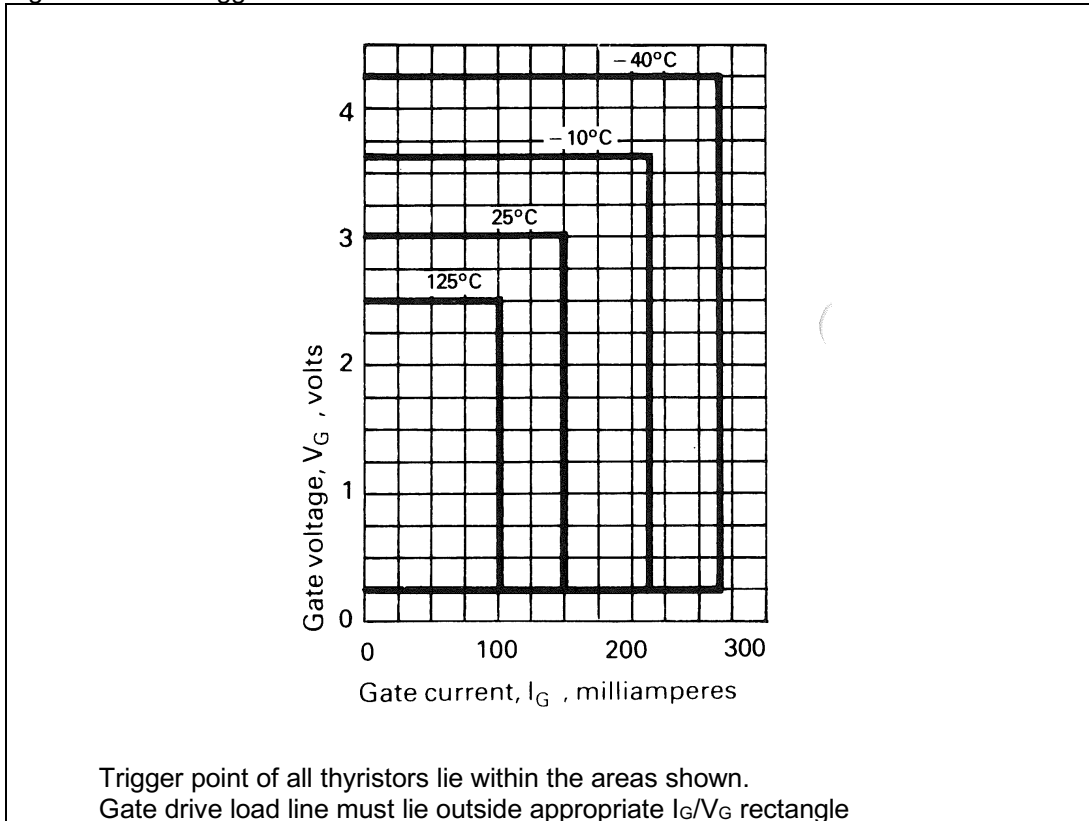


Figure 5 – On-state current vs. case temperature - (Sine wave)

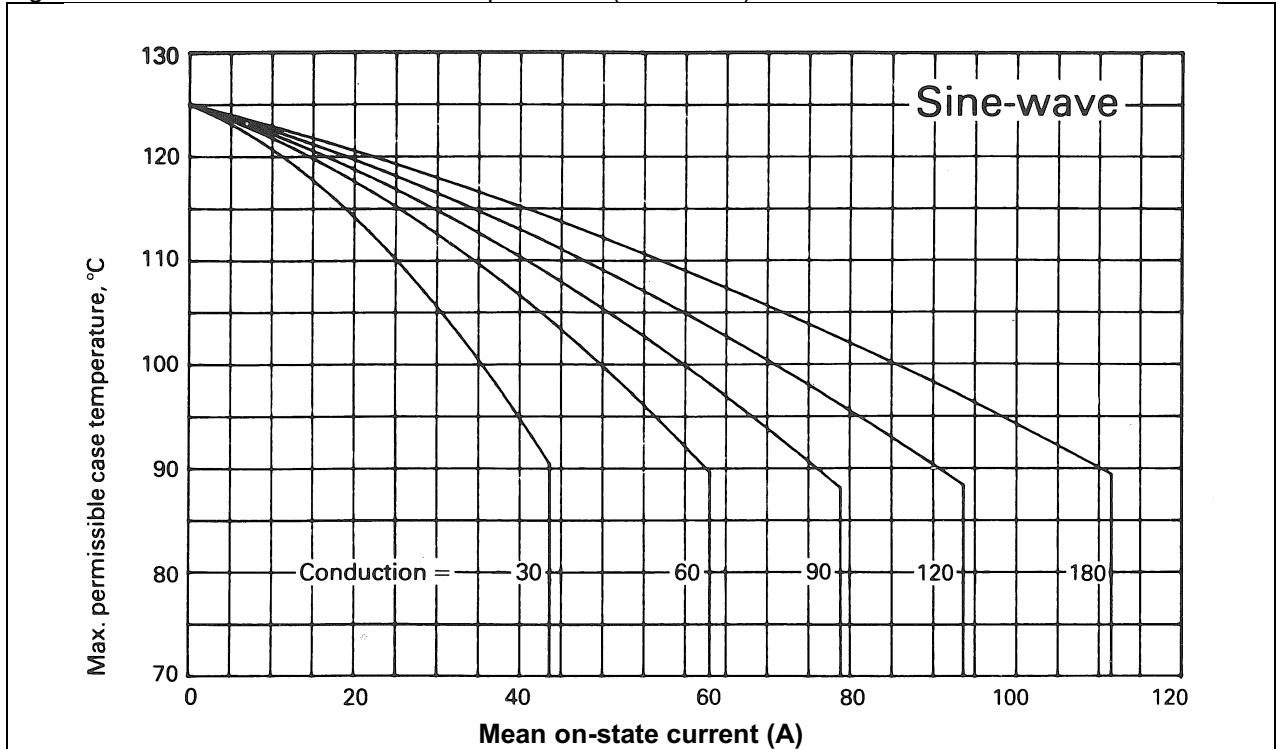


Figure 6 - On-state current vs. Power dissipation - (Sine wave)

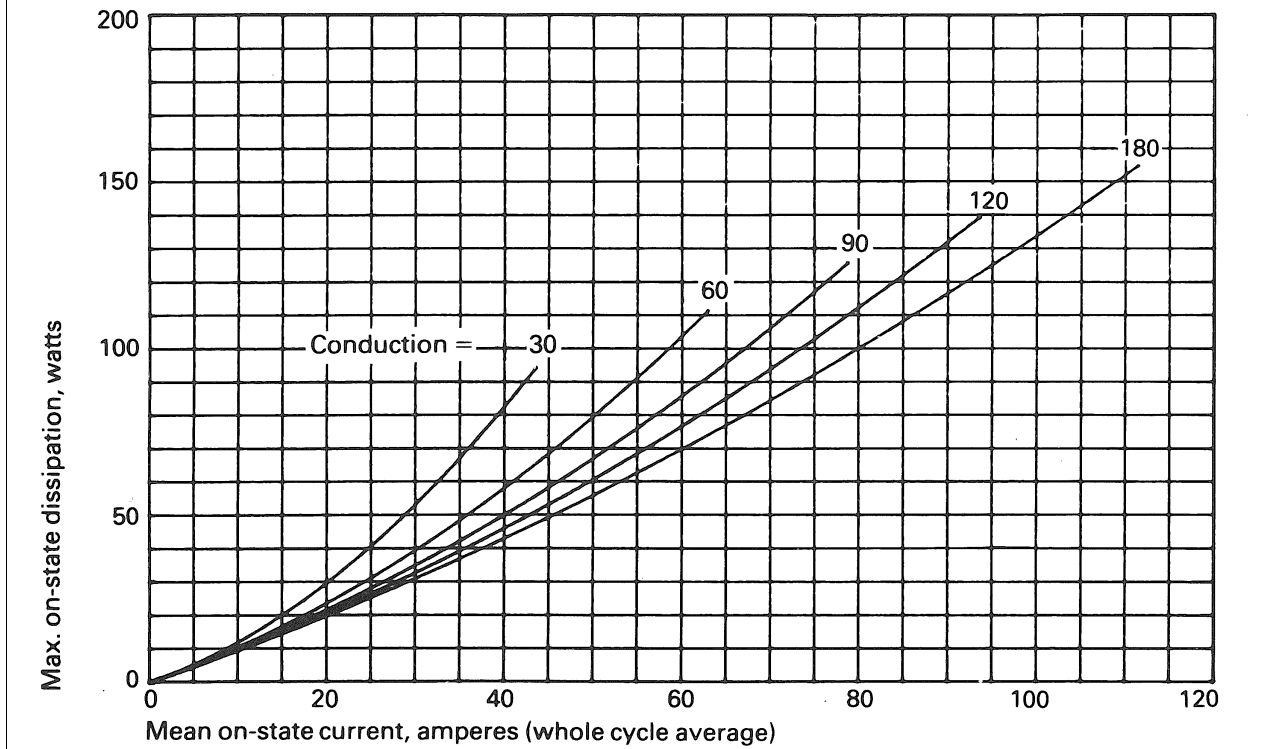


Figure 7 – On-state current vs. case temperature - (Square wave)

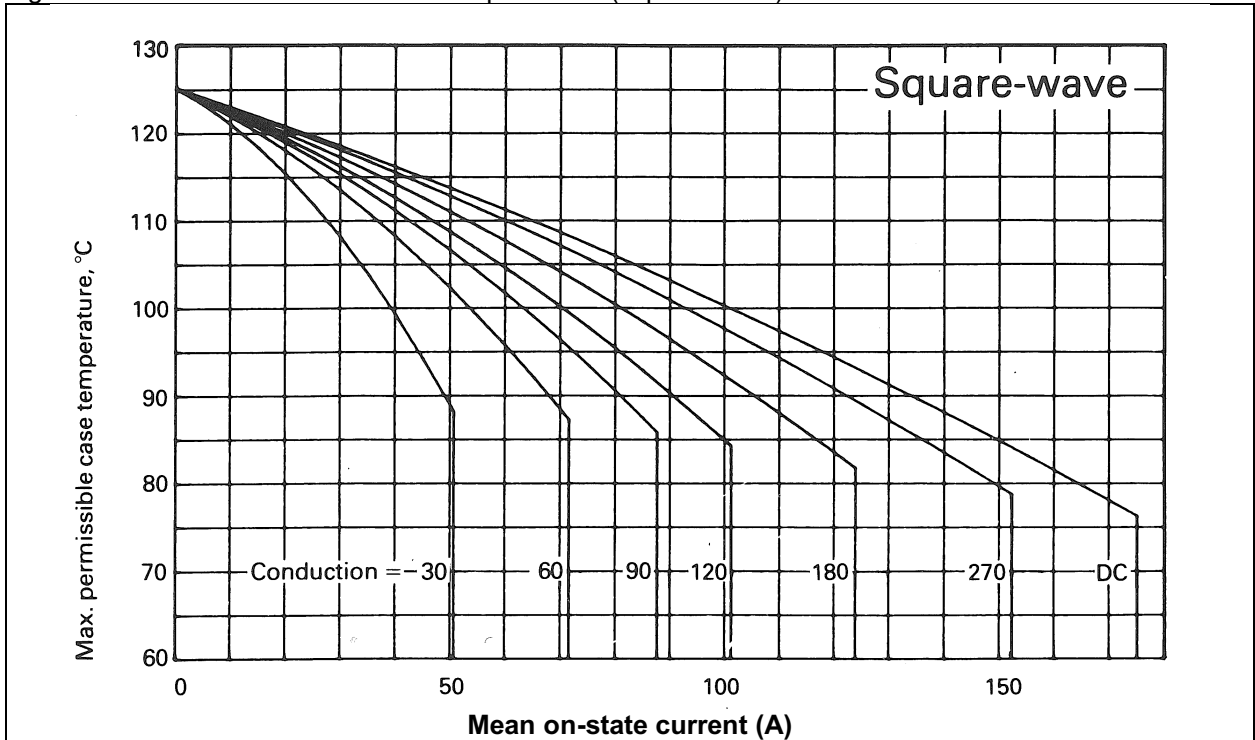


Figure 8 – On-state current vs. Power dissipation - (Square wave)

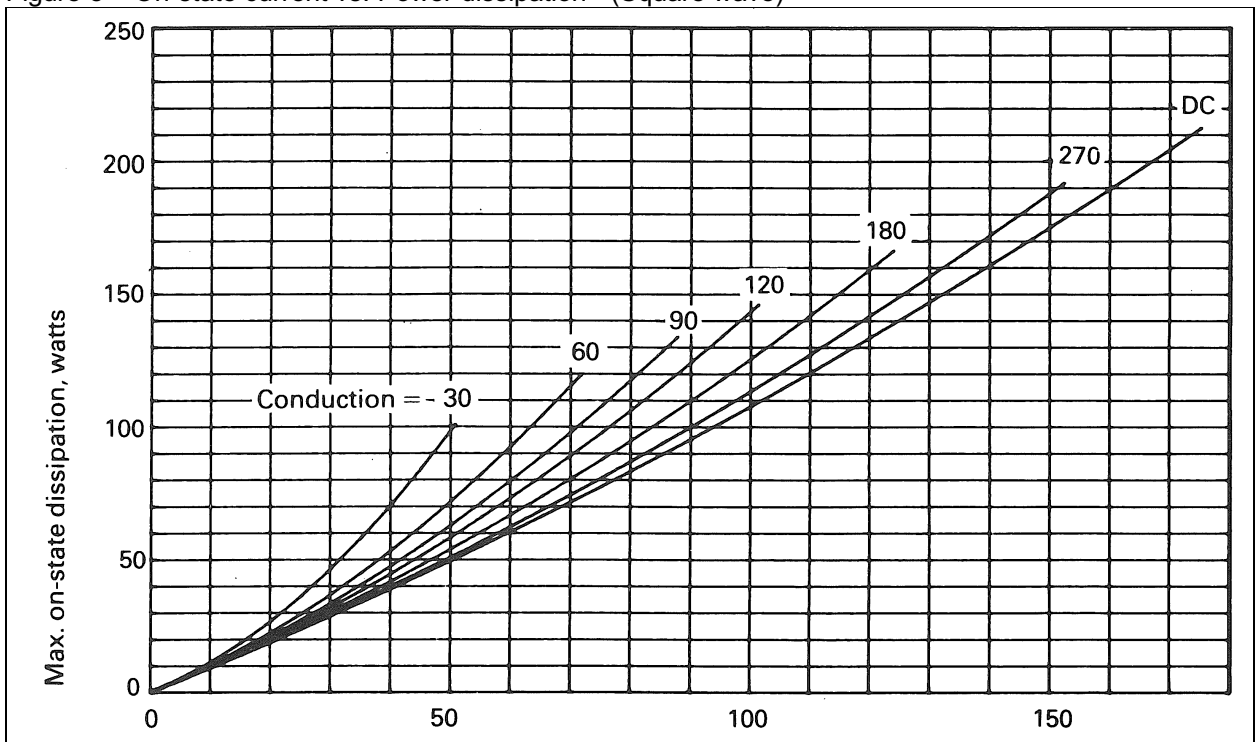
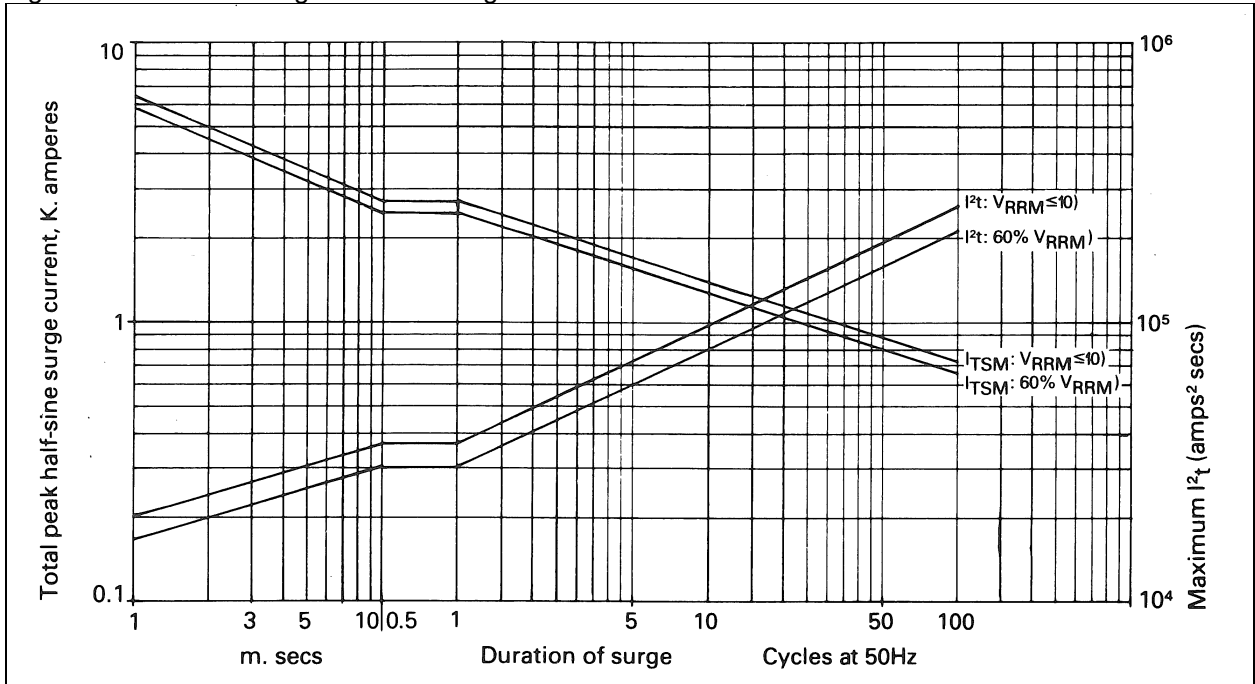
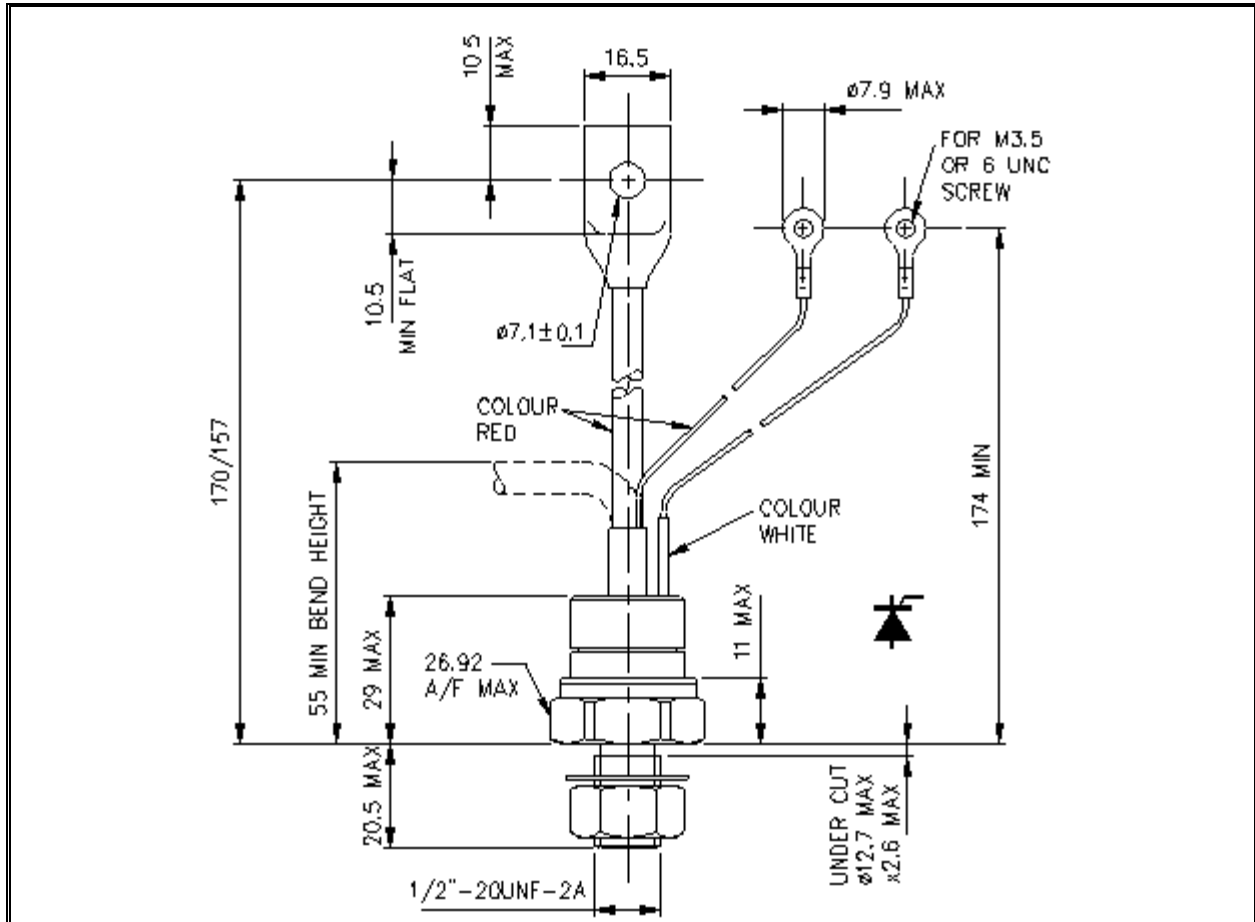


Figure 9 – Maximum surge and I2t Ratings





**Outline Drawing & Ordering Information**



101A231

**ORDERING INFORMATION**

(Please quote 10 digit code as below)

<b>N0180</b> Fixed Type Code	<b>SH</b> Fixed Outline Code	◆ ◆ Off-state Voltage Code $V_{DRM}/100$ 12-16	<b>0</b> Fixed Code
------------------------------------	------------------------------------	---	------------------------

Typical order code: N0180SH140 – 1400V  $V_{RRM}/V_{DRM}$

**IXYS Semiconductor GmbH**  
Edisonstraße 15  
D-68623 Lampertheim  
Tel: +49 6206 503-0  
Fax: +49 6206 503-627  
E-mail: [marcom@ixys.de](mailto:marcom@ixys.de)



**IXYS UK Westcode Ltd**  
Langley Park Way, Langley Park,  
Chippenham, Wiltshire, SN15 1GE.  
Tel: +44 (0)1249 444524  
Fax: +44 (0)1249 659448  
E-mail: [sales@ixysuk.com](mailto:sales@ixysuk.com)

**IXYS Corporation**  
1590 Buckeye Drive  
Milpitas CA 95035-7418  
Tel: +1 (408) 457 9000  
Fax: +1 (408) 496 0670  
E-mail: [sales@ixys.net](mailto:sales@ixys.net)

[www.ixysuk.com](http://www.ixysuk.com)

[www.ixys.com](http://www.ixys.com)

**IXYS Long Beach**  
IXYS Long Beach, Inc  
2500 Mira Mar Ave, Long Beach  
CA 90815  
Tel: +1 (562) 296 6584  
Fax: +1 (562) 296 6585  
E-mail: [service@ixyslongbeach.com](mailto:service@ixyslongbeach.com)

The information contained herein is confidential and is protected by Copyright. The information may not be used or disclosed except with the written permission of and in the manner permitted by the proprietors IXYS UK Westcode Ltd.

© IXYS UK Westcode Ltd.

In the interest of product improvement, IXYS UK Westcode Ltd reserves the right to change specifications at any time without prior notice.

Devices with a suffix code (2-letter or letter/digit/letter combination) added to their generic code are not necessarily subject to the conditions and limits contained in this report.



---

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at [www.littelfuse.com/disclaimer-electronics](http://www.littelfuse.com/disclaimer-electronics).